

### **Features**

- High isolation 5000 VRMS
- Patented coplanar structure DMC-Isolator®
- Various CTR selection available
- AC input with transistor output
- Operating Temperature range 55 °C to 110 °C
- External creepage distance ≥ 7.0mm
- Distance Through Isolation ≥ 0.4mm
- Clearances Distance ≥ 7.5mm (S/SL Type)
- Clearances Distance ≥ 8.0mm (M/SLM Type)
- RoHS and REACH compliance
- Halogen Free compliance (Optional)
- MSL class 1
- Regulatory Approvals
  - ✓ UL UL1577 (E364000)
  - ✓ VDE EN60747-5-5(VDE0884-5)
  - ✓ CQC GB4943.1, GB8898 (14001104781)
  - ✓ IEC62368 (FI/41119)

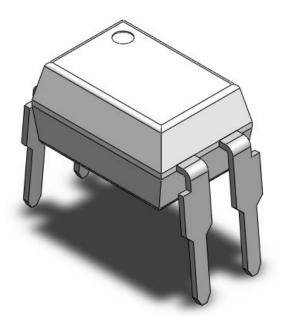
### **Description**

The CT814 series consists of a phototransistor optically coupled to two Infrared-emitting diodes, connected in inverse parallel, in a 4-lead DIP DMC-Isolator® package with different lead forming options.

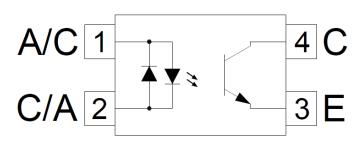
### **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

### **Package Outline**



### **Schematic**



Note: Different lead forming options available. See package dimension.



### Absolute Maximum Ratings $T_A = 25$ °C, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V <sub>RMS</sub>	
Ртот	Total power dissipation	200	mW	
Topr	Operating temperature	-55 ~ +110	°C	
Tstg	Storage temperature	-55 ~ +150	°C	
TsoL	Soldering temperature (For 10 seconds)	260	°C	
Emitter				
lF	Forward current	±60	mA	
I <sub>F</sub> (TRANS)	Peak transient current (≤1µs P.W,300pps)	1	А	
P <sub>D</sub>	Emitter power dissipation	100	mW	
Detector				
PD	Detector power dissipation	150	mW	
B <sub>VCEO</sub>	Collector-Emitter Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	6	V	
Ic	Collector Current	50	mA	



### **Electrical Characteristics** $T_A = 25^{\circ}C$ , unless otherwise specified

### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I <sub>F</sub> =10mA	-	1.24	1.4	V	
Cin	Input Capacitance	f= 1MHz	-	30	-	pF	

### **Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B <sub>VCEO</sub>	Collector-Emitter Breakdown	Ic= 100μA	80	-	-	V	
Bveco	Emitter-Collector Breakdown	I <sub>E</sub> = 100μA	6	-	-	V	
ICEO	Collector-Emitter Dark Current	V <sub>CE</sub> = 20V, I <sub>F</sub> =0mA	-	-	100	nA	

### **Transfer Characteristics**

Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes
	Current Transfer Ratio	CT814	I <sub>F</sub> = ±1mA, V <sub>CE</sub> = 5V 50	20	ı	300	%	
СТР		CT814A		50	-	150		
CIK		CT814B		100	-	300		
	CTR Symmetry		I <sub>F</sub> = ±1mA, V <sub>CE</sub> = 5V	0.7	-	1.3		
Variation	Collector-Emitter Saturation $I_{F=\pm 20mA,\ I_{C=1mA}}$ Voltage		20m4   1m4		0.04	0.2	V	
V CE(SAT)			-	0.04	0.2	V		
Rıo	Isolation Resistance		V <sub>IO</sub> = 500V <sub>DC</sub>	5x10 <sup>10</sup>		-	Ω	
C <sub>IO</sub>	Isolation Capacitance		f= 1MHz	-	0.5	1	pF	

### **Switching Characteristics**

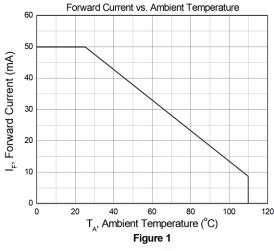
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
t <sub>r</sub>	Rise Time	L- 2mA V 2V D: 1000		6	-		
t <sub>f</sub>	Fall Time	Ic= 2mA, V <sub>CE</sub> = 2V, R <sub>L</sub> = 100Ω	•	8	-	μS	

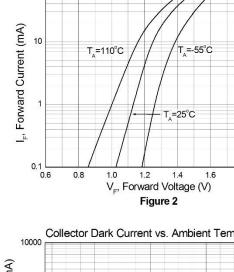


Forward Current vs. Forward Voltage

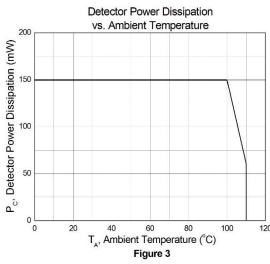
2.0

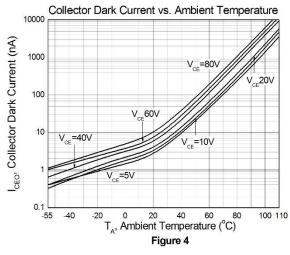
### Typical Characteristic Curves $T_A = 25^{\circ}$ C, unless otherwise specified

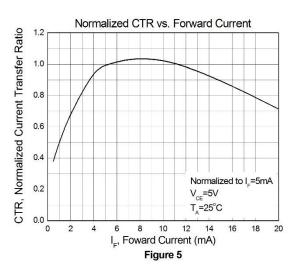


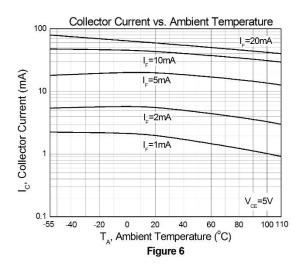


100



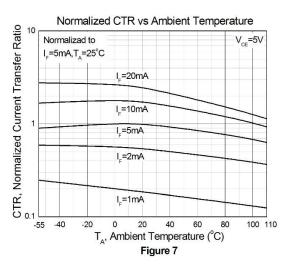


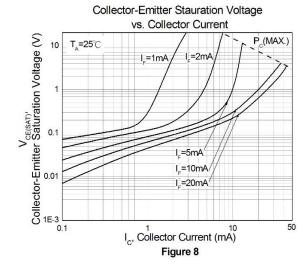


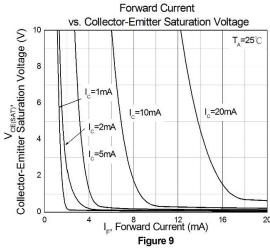


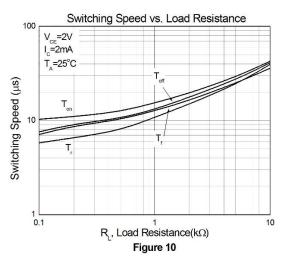


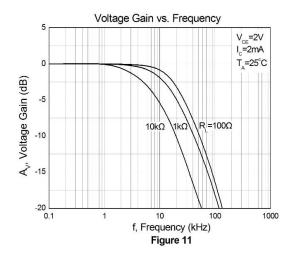
### Typical Characteristic Curves $\tau_A = 25$ °C, unless otherwise specified (Continued)





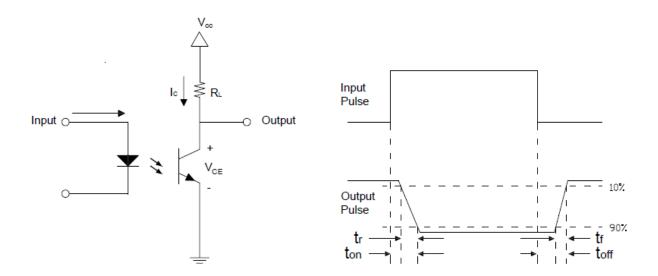








### **Test Circuit**

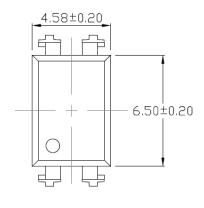


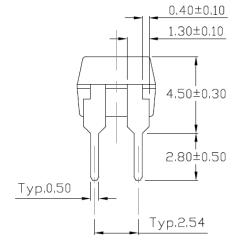
**Figure 12: Switching Time Test Circuits** 

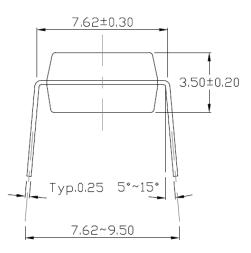


### Package Dimension Dimensions in mm unless otherwise stated

### Standard DIP - Through Hole

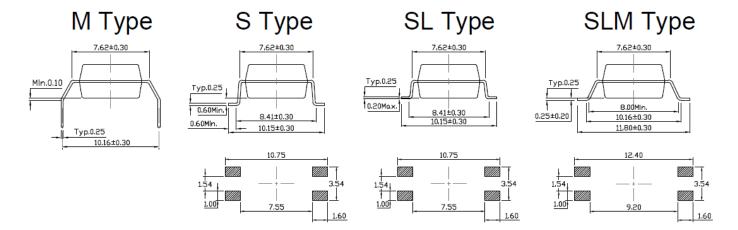






### **Forming Option**







### **Marking Information**



Note:

CT : Denotes "CT Micro"

814 : Part Number

V : VDE Safety Mark Option(Blank, V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code

### **Ordering Information**

### CT814X(V)(Y)(Z)-G

CT = Denotes "CT Micro"

814 = Part Number

Y = Lead Form Option (Blank, S, SL, M or SLM)

Z = Tape and Reel Option (Blank, T1 or T2)

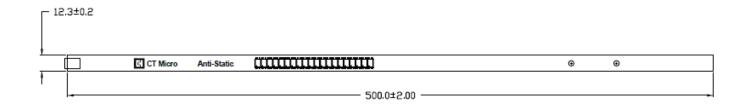
G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

Option	Option Description	
None	Standard 4 Pin DIP	100 Units/Tube
М	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1500 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1500 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1500 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	1500 Units/Reel
SLM(T2) Surface Mount (Gullwing) Lead Forming – With Option 2 Taping		1500 Units/Reel

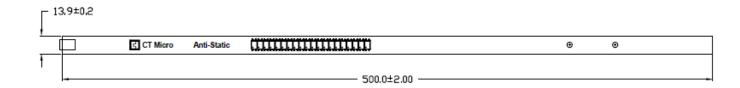


### Carrier Specifications Dimensions in mm unless otherwise stated

### **Tube Option Standard DIP**



### **Tube Option M Type**

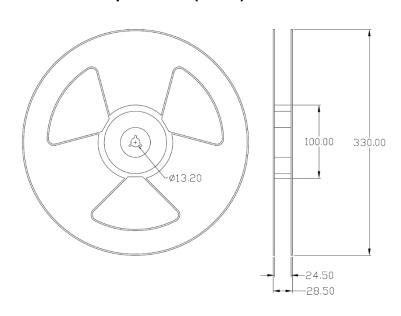


### Reel Dimension All dimensions are in mm, unless otherwise stated

### **Option S(T1/T2) & SL(T1/T2)**

# 100.00 330.00 \$\phi\_{13.20}\$ -16.50 -20.50

### Option SLM(T1/T2)

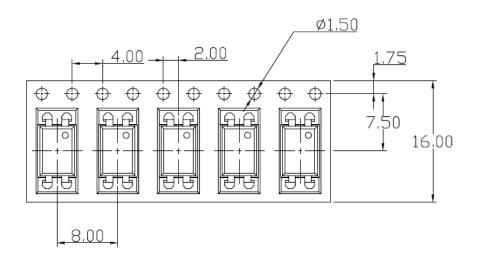


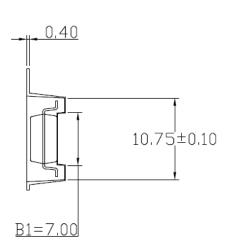


### Carrier Tape Specifications Dimensions in mm unless otherwise stated

### Option S(T1) & SL(T1)

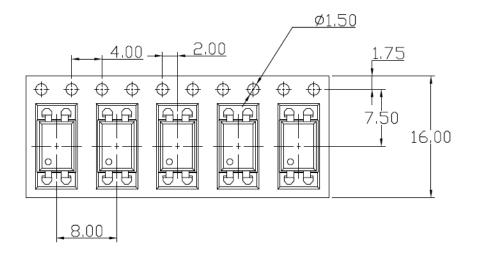
### Input Direction

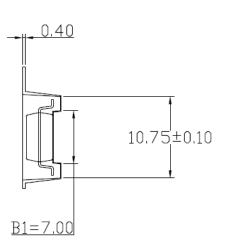




### Option S(T2) & SL(T2)

### Input Direction

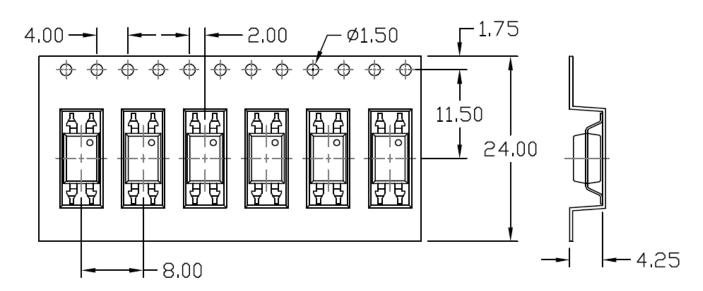






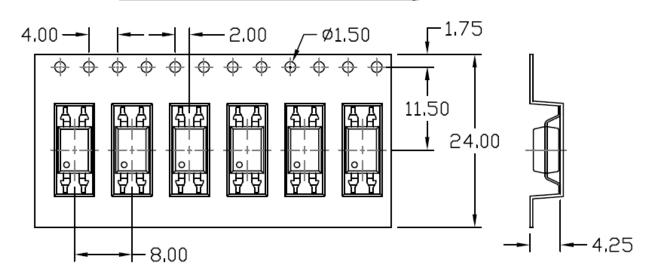
### **Option SLM(T1)**

### Input Direction



### **Option SLM(T2)**

### Input Direction





### Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

### Wave soldering (Follow the JEDEC standard JESD22-A111)

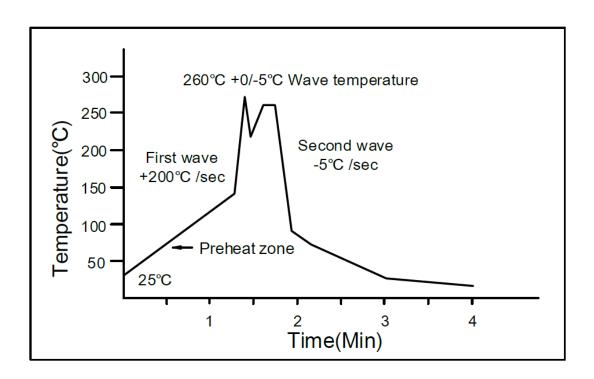
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature: 25 to 140°C.

Preheat time: 30 to 80 sec.

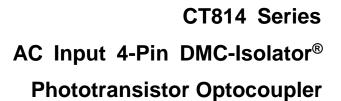


### Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process.

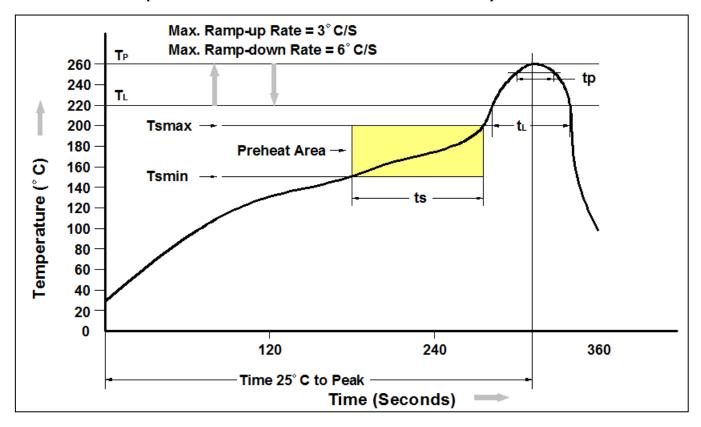
One time soldering is recommended. Temperature: 350±10°C

Time: 5 sec max.





### Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t <sub>P</sub> )	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



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